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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>			<b>Application Number</b>	Unassigned
Date Submitted: June 14, 2005			<b>Filing Date</b>	6/14/2005
(use as many sheets as necessary)			<b>First Named Inventor</b>	Yasuhiro OKAMOTO
			<b>Group Art Unit</b>	Unassigned
			<b>Examiner Name</b>	Unassigned
<b>Sheet</b>	1	of 1	<b>Attorney Docket Number</b>	029437-0108

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
	A1	2002-0005528	A1	Masaki NAGAHARA	01/17/2002	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	A2	JP	09-307097	A	Sony Corp.	11/28/1997		A
	A3	JP	2000-100831	A	NEC Corp.	04/07/2000		A
	A4	JP	2000-323495	A	Sony Corp.	11/24/2000		A
	A5	JP	2001-189324	A	Ricoh Co. Ltd.	07/10/2001		A
	A6	JP	2002-359256	A	Fujitsu Ltd.	12/13/2002		A

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
	A7	ANDO et al., "A 110-W AlGaIn/GaN Heterojunction FET on Thinned Sapphire Substrate," IEDM 01, 2001, pp. 381-384.	
	A8	LI et al., "High breakdown voltage GaN HFET with field plate," Electronics Letters, February 1, 2001, Vol. 37, No. 3, pp. 196-197.	
	A9	MISHRA et al., "AlGaIn/GaN HEMTs - An Overview of Device Operation and Applications," Proceedings of the IEEE, June 2002, vol. 90, No. 6, pp. 1022-1031.	
	A10	TAN et al., "The Effect of Dielectric Stress on the Electrical Characteristics of AlGaIn/GaN Heterostructure Field-Effect Transistors (HFETs)," The 10 <sup>th</sup> IEEE International Symposium on Electron Devices for Microwave and Optoelectronic Applications, November 2002, pp. 130-135.	

<b>Examiner Signature</b>	/Sarah Salerno/	<b>Date Considered</b>	/S.K.S./
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